

Dual P-Channel Enhancement Mode Power MOSFET

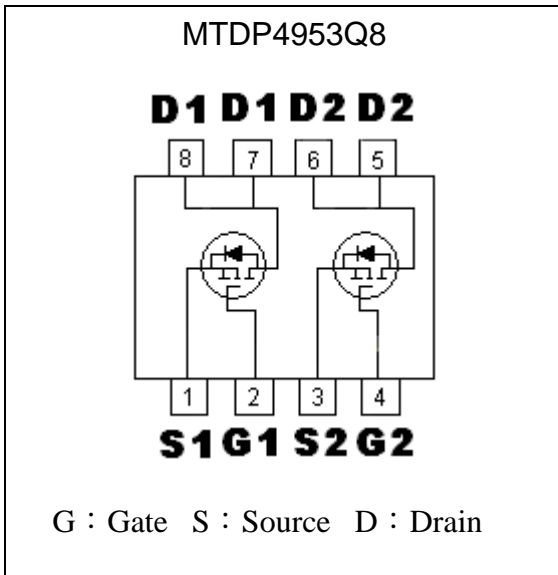
MTDP4953Q8

BVDSS	-30V
ID@TA=25 °C, VGS=-10V	-5.3A
RDSON@VGS=-10V, ID=-5A	52mΩ (typ)
RDSON@VGS=-4.5V, ID=-4A	90mΩ (typ)

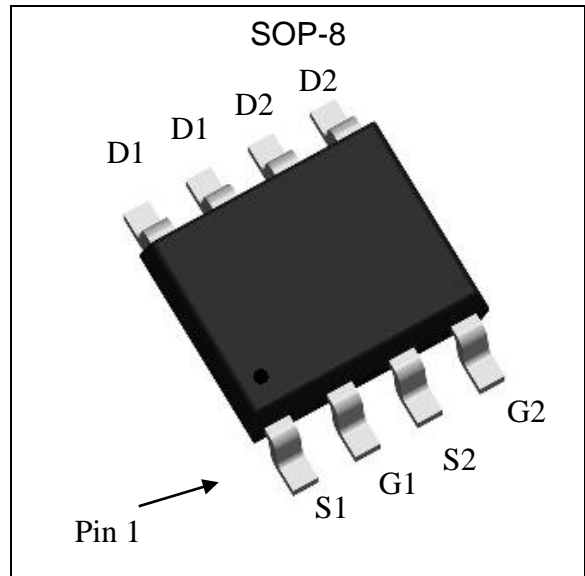
Features

- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Pb-free lead plating and halogen-free package

Equivalent Circuit

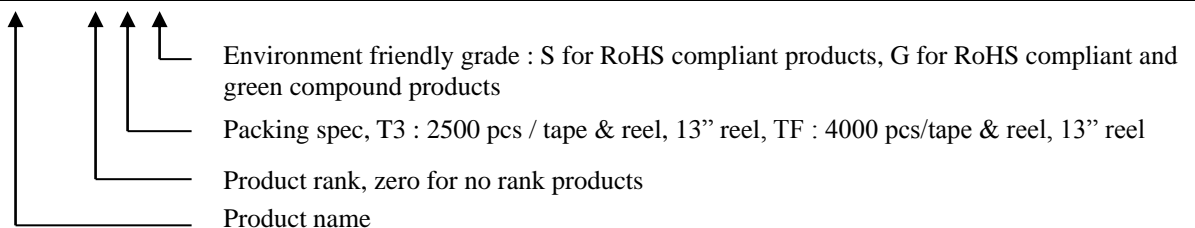


Outline



Ordering Information

Device	Package	Shipping
MTDP4953Q8-0-T3-G	SOP-8 (Pb-free lead plating and halogen-free package)	2500 pcs / tape & reel
MTDP4953Q8-0-TF-G	SOP-8 (Pb-free lead plating and halogen-free package)	4000 pcs / tape & reel





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	-30	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current @T _A =25 °C (Note 1)	I _D	-5.3	A
Continuous Drain Current @T _A =70 °C (Note 1)		-4.2	
Pulsed Drain Current (Note 2)	I _{DM}	-20	
Total Power Dissipation (Note 1)	P _D	2	W
Linear Derating Factor		0.02	W / °C
Operating Junction and Storage Temperature Range	T _j ; T _{stg}	-55~+150	°C
Thermal Resistance, Junction-to-Ambient (Note 1)	R _{th,ja}	62.5	°C/W

Note : 1.Surface mounted on 1 in² copper pad of FR-4 board, t≤10s.
 2.Pulse width ≤300µs, duty cycle≤2%

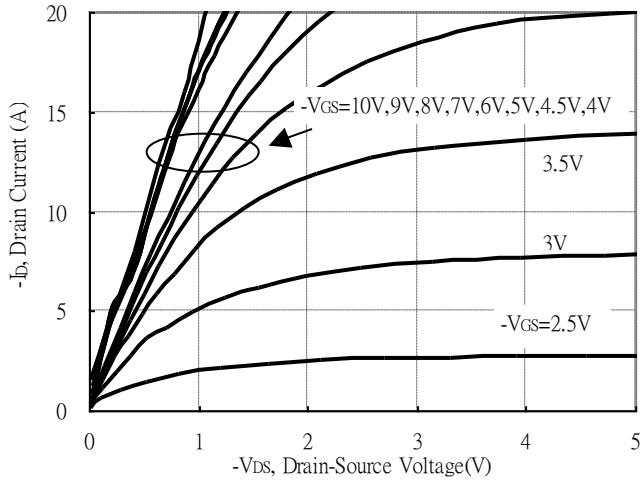
Electrical Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-30	-	-	V	V _{GS} =0V, I _D =-250µA
V _{GS(th)}	-1	-	-2.5		V _{DS} =V _{GS} , I _D =-250µA
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	-1	µA	V _{DS} =-24V, V _{GS} =0V
*R _{DS(ON)}	-	52	65	mΩ	I _D =-5A, V _{GS} =-10V
	-	90	120		I _D =-4A, V _{GS} =-4.5V
*G _{FS}	-	7.9	-	S	V _{DS} =-5V, I _D =-5A
Dynamic					
C _{iss}	-	453	-	pF	V _{DS} =-15V, V _{GS} =0V, f=1MHz
C _{oss}	-	59	-		
C _{rss}	-	56	-		
*t _{d(ON)}	-	4.6	-	ns	V _{DS} =-15V, I _D =-1A, V _{GS} =-10V, R _G =3.3Ω
*t _r	-	7	-		
*t _{d(OFF)}	-	33	-		
*t _f	-	5	-		
*Q _g	-	11	-	nC	V _{DS} =-15V, I _D =-5.3A, V _{GS} =-10V
*Q _{gs}	-	1.1	-		
*Q _{gd}	-	2.7	-		
R _g	-	11	-	Ω	f=1MHz
Source-Drain Diode					
*V _{SD}	-	-0.83	-1.2	V	V _{GS} =0V, I _S =-1.7A
*Q _{rr}	-	8.1	-	nC	I _F =-1.7A, dI _F /dt=100A/µs
*t _{rr}	-	3.6	-	ns	

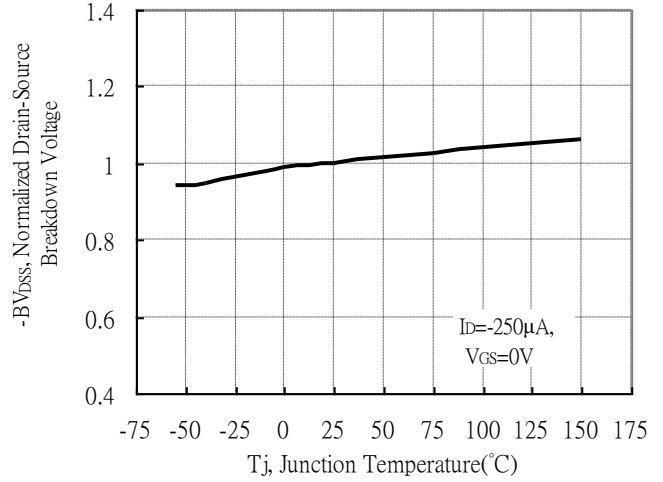
*Pulse Test : Pulse Width ≤300µs, Duty Cycle≤2%

Typical Characteristics

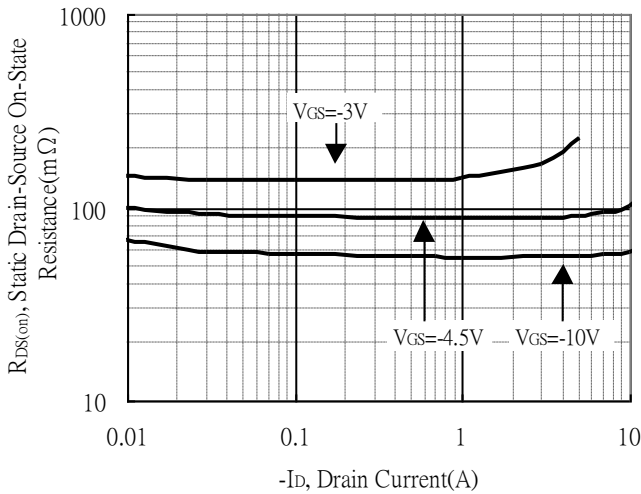
Typical Output Characteristics



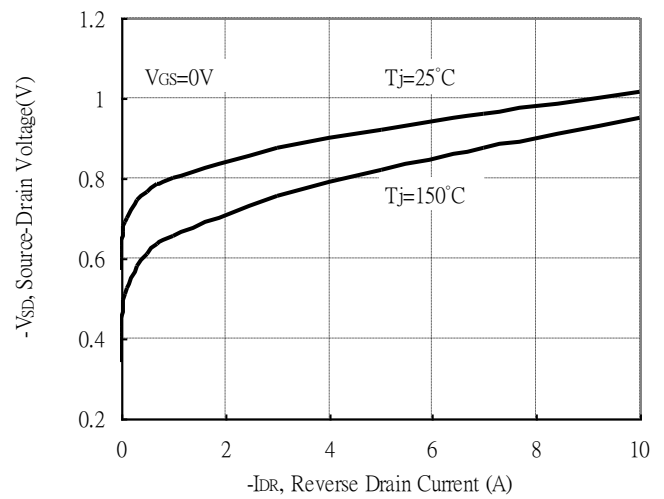
Brekdown Voltage vs Ambient Temperature



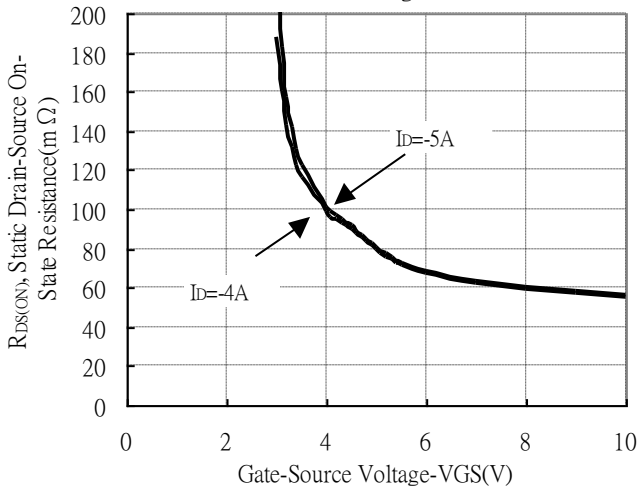
Static Drain-Source On-State resistance vs Drain Current



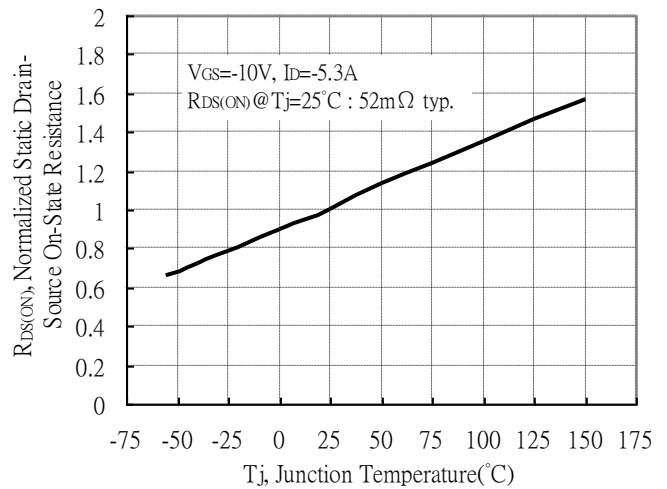
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

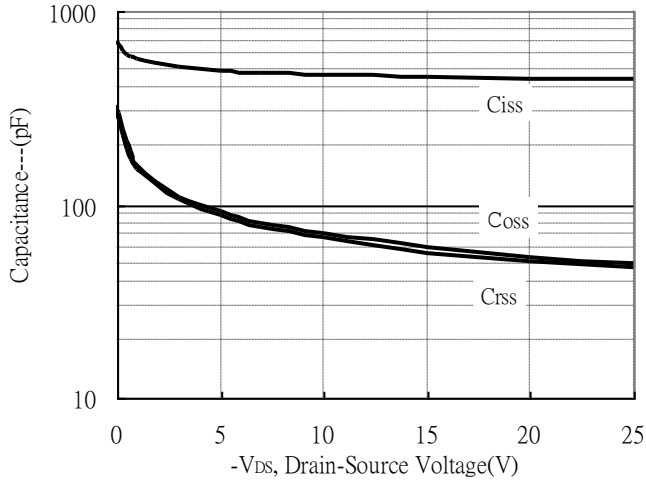


Drain-Source On-State Resistance vs Junction Temperature

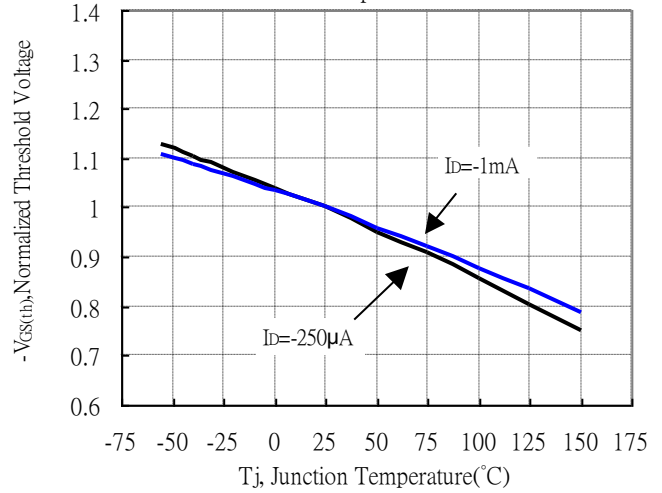


Typical Characteristics (Cont.)

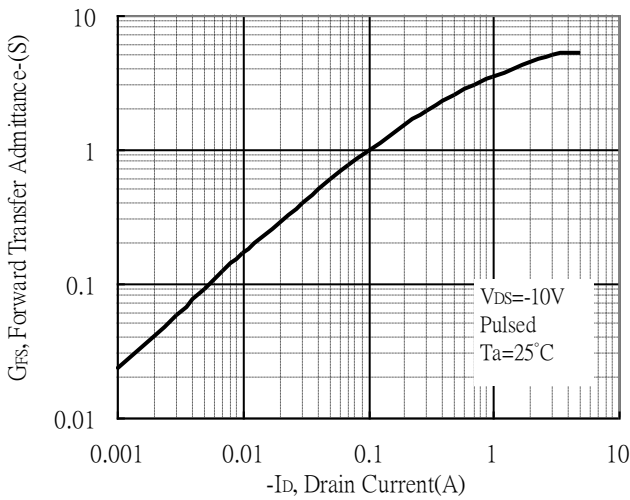
Capacitance vs Drain-to-Source Voltage



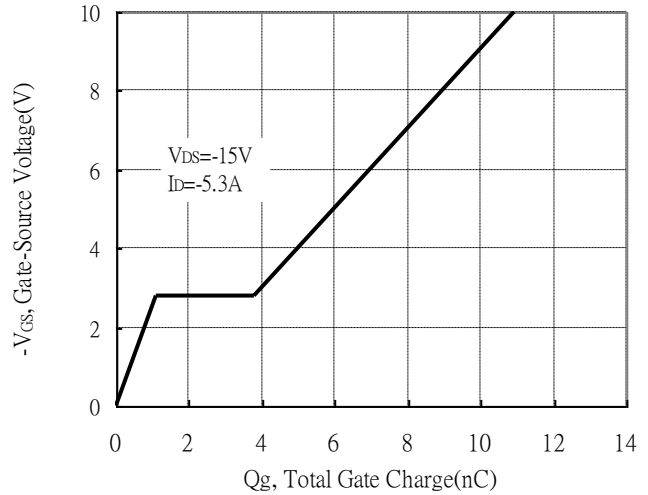
Normalized Threshold Voltage vs Junction Temperature



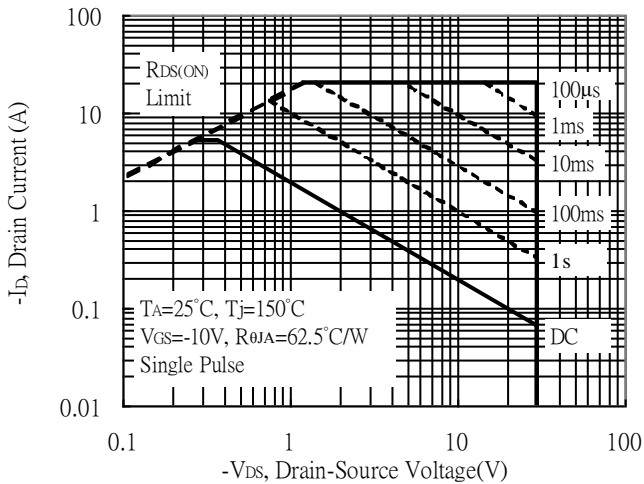
Forward Transfer Admittance vs Drain Current



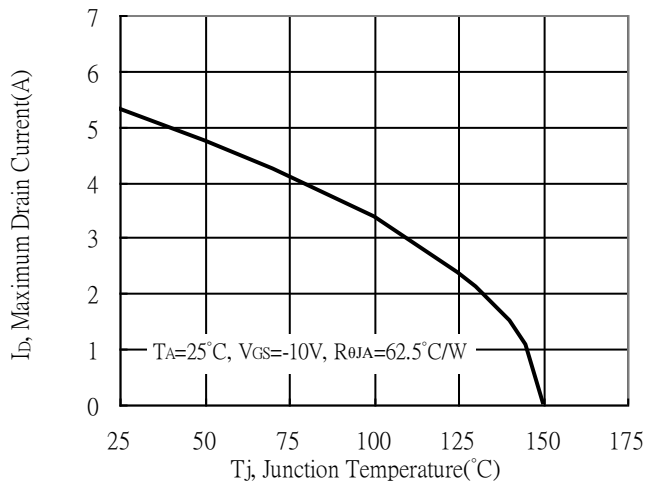
Gate Charge Characteristics



Maximum Safe Operating Area

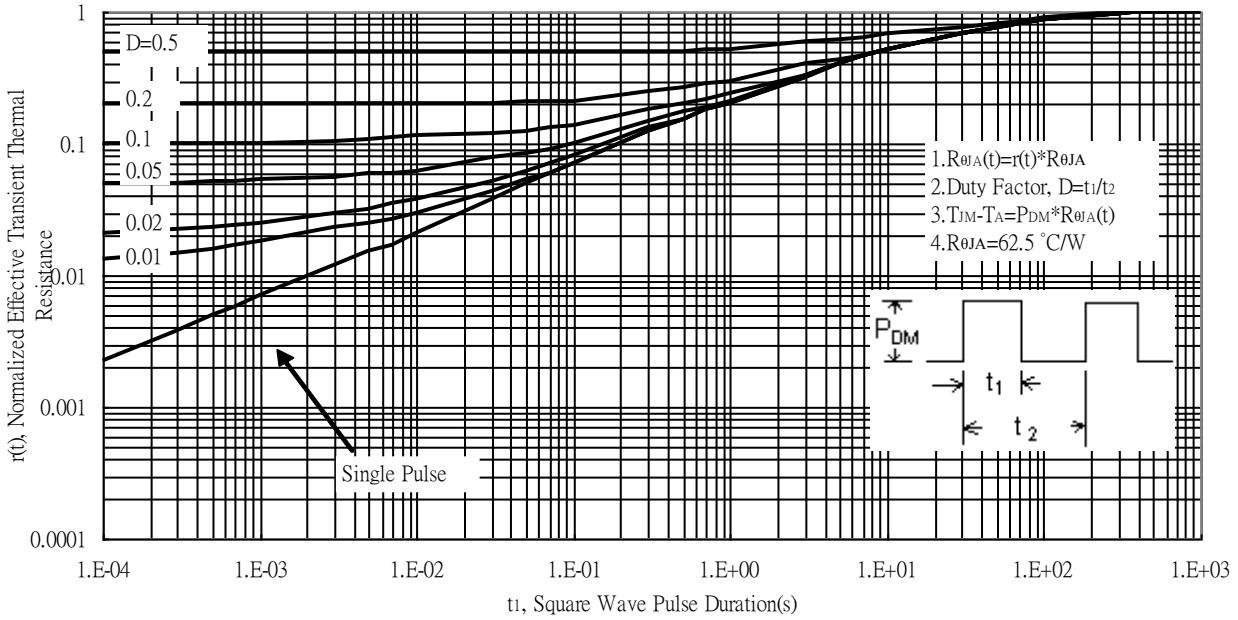


Maximum Drain Current vs Junction Temperature

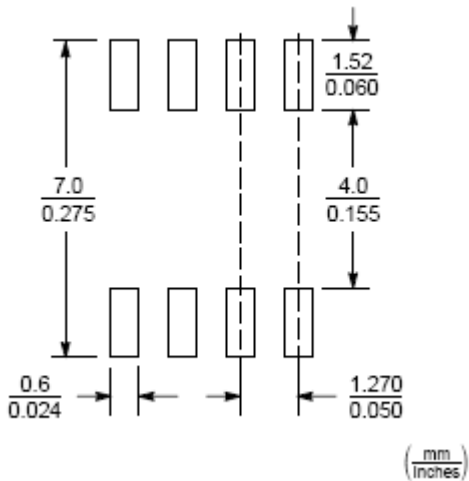


Typical Characteristics (Cont.)

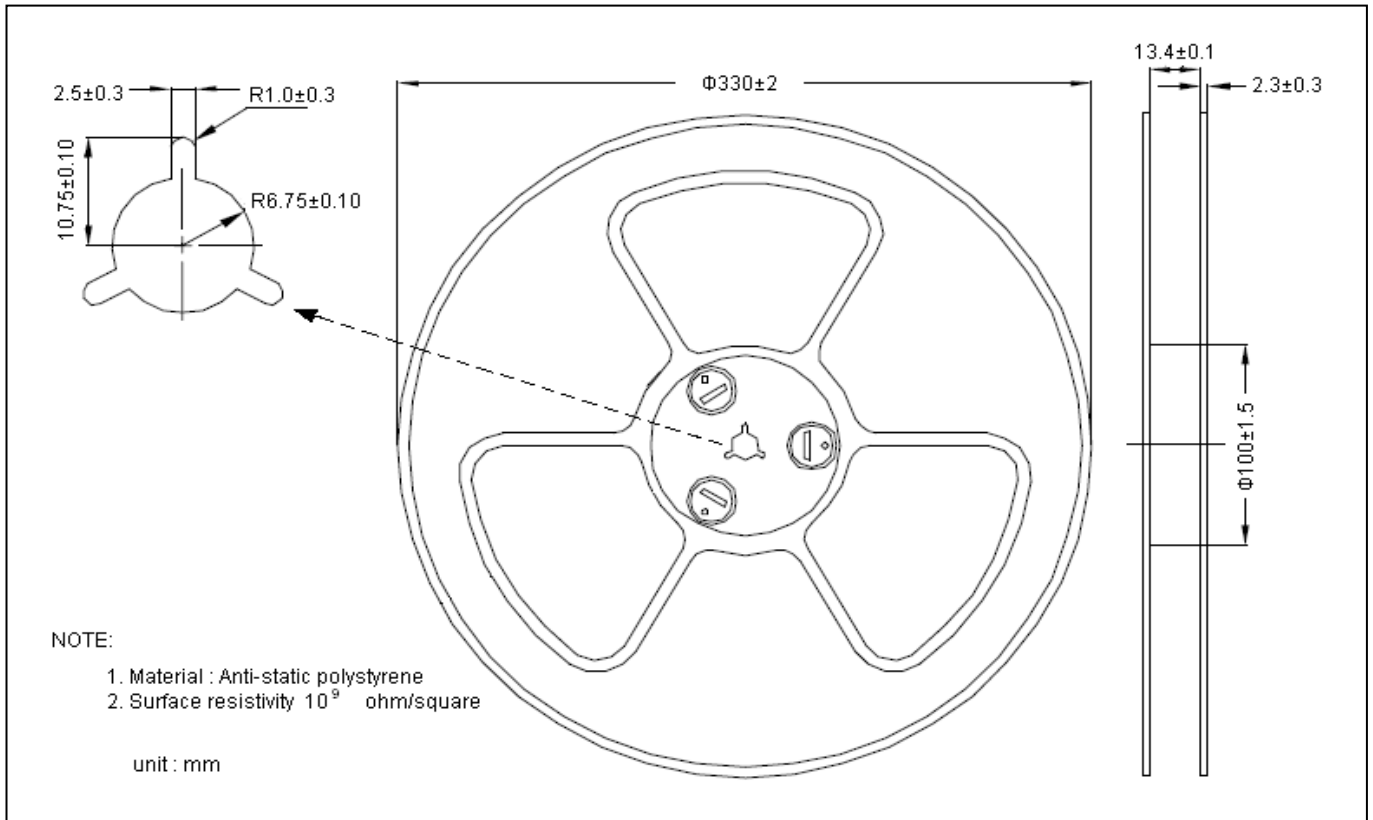
Transient Thermal Response Curves



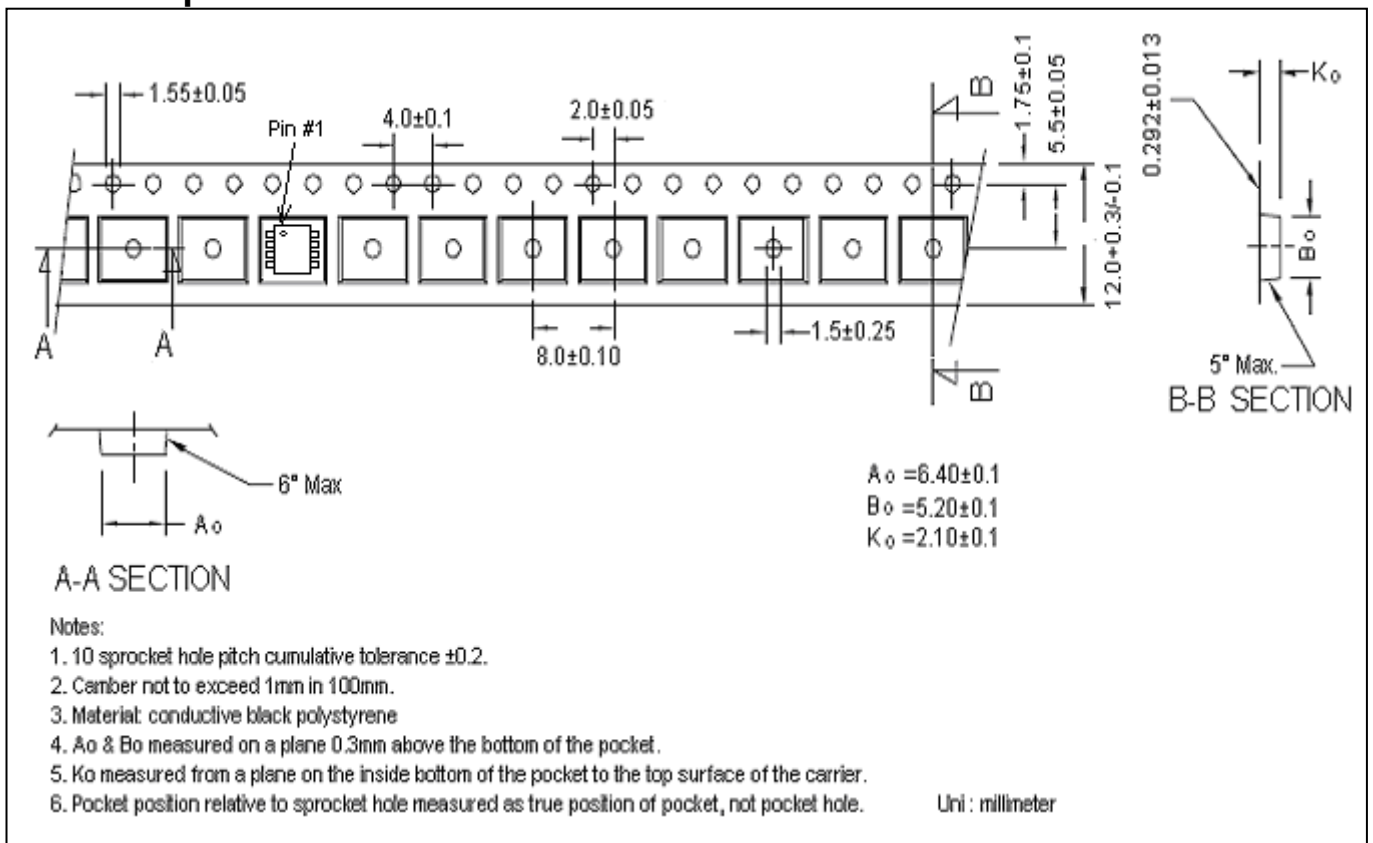
Recommended Soldering Footprint



Reel Dimension



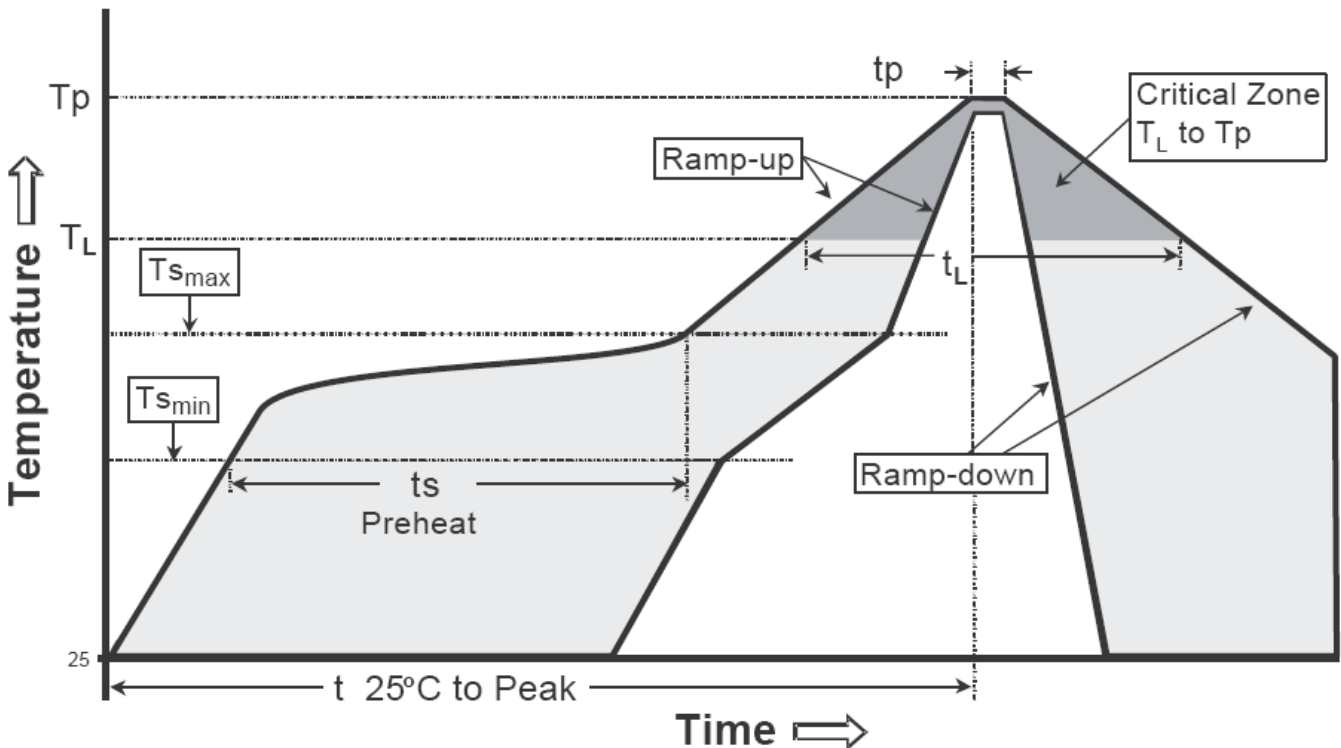
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

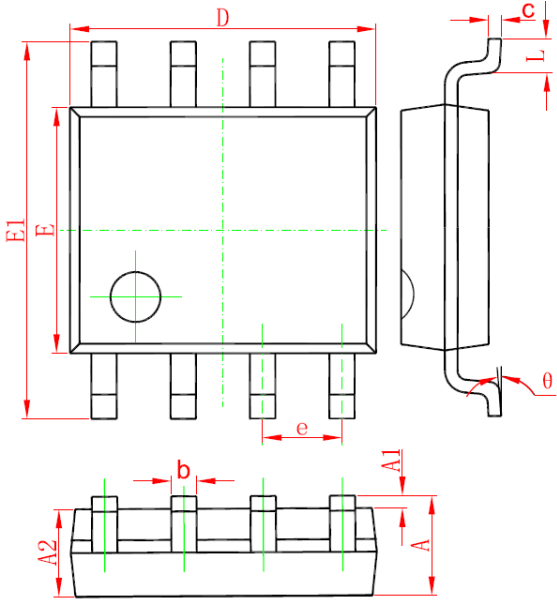
Recommended temperature profile for IR reflow



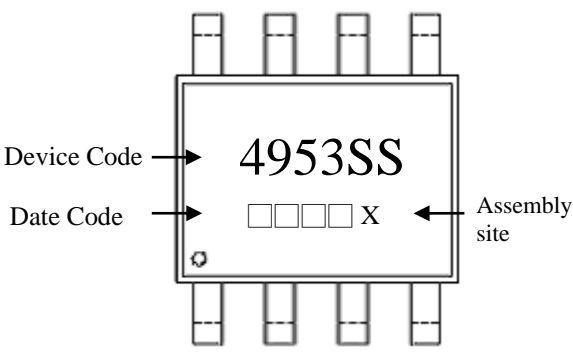
Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOP-8 Dimension



Marking:



Device Code → **4953SS**

Date Code → □□□□ X ← Assembly site

Date Code(counting from left to right) :

1st code: year code, the last digit of Christian year

2nd code : month code, Jan→A, Feb→B, Mar→C, Apr→D
 May→E, Jun→F, Jul→G, Aug→H, Sep→J,
 Oct→K, Nov→L, Dec→M

3rd and 4th codes : production serial number, 01~99

Assembly site : blank for site 1, G for site 2

8-Lead SOP-8 Plastic Package
 CYStek Package Code: Q8

*: Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069	E	3.800	4.000	0.150	0.157
A1	0.100	0.250	0.004	0.010	E1	5.800	6.200	0.228	0.244
A2	1.350	1.550	0.053	0.061	e	*1.270		*0.050	
b	0.330	0.510	0.013	0.020	L	0.400	1.270	0.016	0.050
c	0.170	0.250	0.006	0.010	θ	0°	8°	0°	8°
D	4.700	5.100	0.185	0.200					

- Notes:** 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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